

**IN THE CLAIMS:**

Please delete Claims 2, 15. Furthermore, please enter the following clean version of amend Claims 1, 3, 7, 14, 16, 17, 19, and 20:

B1 1. A method of fabricating an electronic device formed on a semiconductor wafer, comprising the steps of:

forming a layer of a first material in a fixed position relative to the wafer, wherein the first material has a dielectric constant less than 3.6;

5 forming a photoresist layer in a fixed position relative to the layer of the first material;

forming at least one void through the layer of the first material in response to the photoresist layer, thereby forming a polymeric residue in response to the photoresist layer ;

10 subjecting the semiconductor wafer to a plasma which incorporates a gas which includes hydrogen so as to remove the photoresist layer; and

removing the polymeric residue, the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of hydrogen, oxygen, and fluorine.

B2 3. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a wet etch chemistry.

B3 7. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a combination of dilute hydrofluoric acid and an organic acid.

B4 14. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a dry plasma.

B5 16. The method of claim 1:  
wherein the hydrogen in the mixture is provided from a hydrogen source selected from a group consisting of  $H_2$ ,  $NH_3$ ,  $N_2H_2$ ,  $H_2S$ , and  $CH_4$ ; and  
wherein the fluorine in the mixture is provided from a fluorine source selected  
5 from a group consisting of  $CF_4$ ,  $C_2F_6$ ,  $CHF_3$ ,  $CH_2F_2$ ,  $SF_6$ ,  $CH_3F$ , and  $NF_3$ .

17. The method of claim 1 wherein the mixture further comprises an inert gas.

B6 19. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of at least 50% hydrogen, and approximately 2-20% oxygen and approximately 2-6% fluorine.

20. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of approximately 80%  $NH_3$ , approximately 10-15%  $N_2$ , approximately 2-7%  $O_2$ , and approximately 2-6%  $CF_4$ .